NPN Epitaxial Planar Silicon Transistor

2SC3071



# High h<sub>FE</sub>, Low-Frequency General-Purpose Amplifier Applications

## Applications

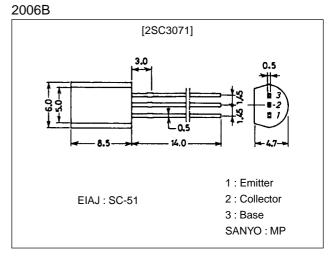
· Low-frequency, general-purpose amplifier., various drivers, muting circuit.

### Features

- $\cdot$  High DC current gain (h<sub>FE</sub>=500 to 2000).
- · High breakdown voltage ( $V_{CEO} \ge 100V$ ).
- · Low collector-to-emitter saturation voltage  $(V_{1}, \ldots, C_{n}, S_{n})$
- $(V_{CE(sat)} \leq 0.5V).$
- $\cdot$  High V<sub>EBO</sub> (V<sub>EBO</sub> $\geq$ 15V).

## **Package Dimensions**

unit:mm



## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

| Parameter                    | Symbol           | Conditions | Ratings     | Unit |
|------------------------------|------------------|------------|-------------|------|
| Collector-to-Base Voltage    | V <sub>CBO</sub> |            | 120         | V    |
| Collector-to-Emitter Voltage | V <sub>CEO</sub> |            | 100         | V    |
| Emitter-to-Base Voltage      | V <sub>EBO</sub> |            | 15          | V    |
| Collector Current            | IC               |            | 200         | mA   |
| Collector Current (Pulse)    | ICP              |            | 300         | mA   |
| Base Current                 | Ι <sub>Β</sub>   |            | 40          | mA   |
| Collector Dissipation        | PC               |            | 1           | W    |
| Junction Temperature         | Tj               |            | 150         | °C   |
| Storage Temperature          | Tstg             |            | -55 to +150 | °C   |

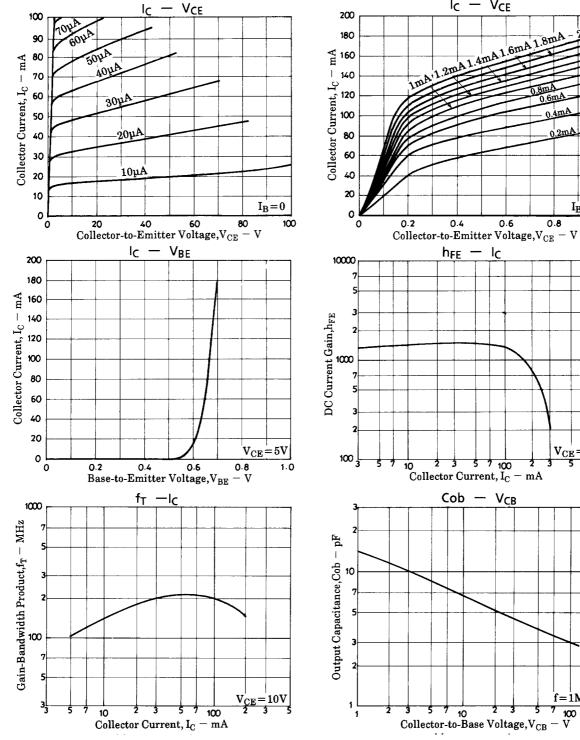
#### **Electrical Characteristics at Ta = 25°C**

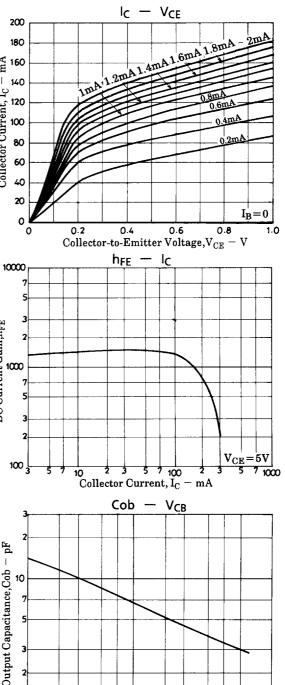
| Parameter                | Symbol            | Conditions                                 | Ratings |     |      | Unit |
|--------------------------|-------------------|--|---------|-----|------|------|
|                          |                   |  | min     | typ | max  |      |
| Collector Cutoff Current | ICBO              | V <sub>CB</sub> =80V, I <sub>E</sub> =0    |         |     | 0.1  | μΑ   |
| Emitter Cutoff Current   | IEBO              | V <sub>EB</sub> =10V, I <sub>C</sub> =0    |         |     | 0.1  | μΑ   |
| DC Current Gain          | hFE1              | V <sub>CE</sub> =5V, I <sub>C</sub> =10mA  | 500     |     | 2000 |      |
|                          | h <sub>FE</sub> 2 | V <sub>CE</sub> =5V, I <sub>C</sub> =100mA | 400     |     |      |      |
| Gain-Bandwidth Product   | fT                | V <sub>CE</sub> =10V, I <sub>C</sub> =10mA |         | 150 |      | MHz  |
| Output Capacitance       | Cob               | V <sub>CB</sub> =10V, f=1MHz               |         | 6.5 |      | pF   |

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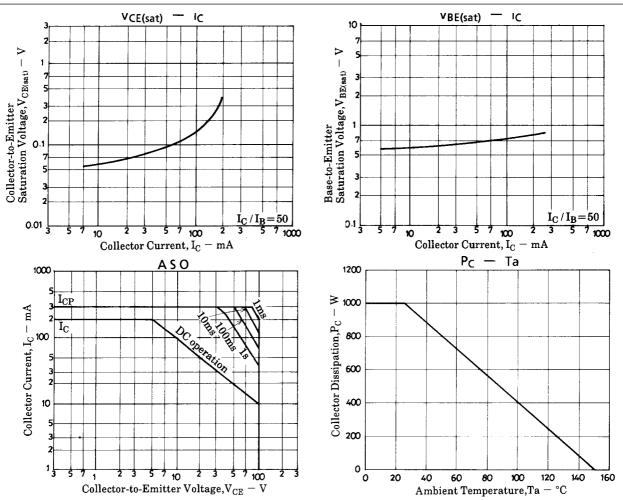
SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

| Parameter                               | Symbol               | Conditions                                 | Ratings |      |     | Unit |
|---|----------------------|--|---------|------|-----|------|
|   |                      |  | min     | typ  | max | Unit |
| Collector-to-Emitter Saturation Voltage | VCE(sat)             | I <sub>C</sub> =100mA, I <sub>B</sub> =2mA |         | 0.15 | 0.5 | V    |
| Base-to-Emitter Saturation Voltage      | V <sub>BE(sat)</sub> | I <sub>C</sub> =100mA, I <sub>B</sub> =2mA |         | 0.85 | 1.2 | V    |
| Collector-to-Base Breakdown Voltage     | V(BR)CBO             | I <sub>C</sub> =10μΑ, I <sub>E</sub> =0    | 120     |      |     | V    |
| Collector-to-Emitter Breakdown Voltage  | V(BR)CEO             | I <sub>C</sub> =1mA, R <sub>BE</sub> =∞    | 100     |      |     | V    |
| Emitter-to-Base Breakdown Voltage       | V(BR)EBO             | I <sub>E</sub> =10μΑ, I <sub>C</sub> =0    | 15      |      |     | V    |





f = 1 M H z



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